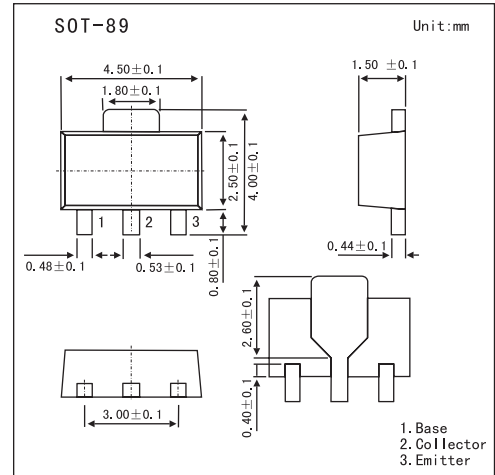


PNP Transistor

2SA1664

■ Features

- Collector current $I_c = -0.8A$
- Power dissipation $P_c = 0.5W$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-35	V
Collector-emitter voltage	V_{CE0}	-30	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_c	-0.8	A
Collector power dissipation	P_c	0.5	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_c = -1mA, I_E = 0$	-35			V
Collector-emitter breakdown voltage	V_{CE0}	$I_c = -10mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	V_{EB0}	$I_E = -1mA, I_c = 0$	-5			V
Collector-base cutoff current	I_{CB0}	$V_{CB} = -35V, I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EB0}	$V_{EB} = -5V, I_c = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_c = -100mA$	100		320	
		$V_{CE} = -1V, I_c = -700mA$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -20mA$			-0.7	V
Base emitter voltage	V_{BE}	$V_{CE} = -1V, I_c = -10mA$	-0.5		-0.8	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		120		MHz
Transition frequency	f_T	$V_{CE} = -5V, I_c = -10mA$		19		pF

■ h_{FE} Classification

Marking	RO	RY
Rank	O	Y
h_{FE}	100~200	160~320